

Title (en)
REDUCED RESIDUAL FORMATION IN ETCHED MULTI-LAYER STACKS

Title (de)
REDUZIERTE RESTBILDUNG IN GEÄTZTEN MEHRSCICHTSTAPELN

Title (fr)
FORMATION RÉSIDUELLE RÉDUITE DANS DES EMPILEMENTS MULTICOUCHES GRAVÉS

Publication
EP 2188831 A1 20100526 (EN)

Application
EP 08795566 A 20080825

Priority

- US 2008010063 W 20080825
- US 95789107 P 20070824
- US 19695908 A 20080822

Abstract (en)
[origin: US2009053535A1] A multi-layer stack for imprint lithography is formed by applying a first polymerizable composition to a substrate, polymerizing the first polymerizable composition to form a first polymerized layer, applying a second polymerizable composition to the first polymerized layer, and polymerizing the second polymerizable composition to form a second polymerized layer on the first polymerized layer. The first polymerizable composition includes a polymerizable component with a glass transition temperature less than about 25° C., and the first polymerized layer is substantially impermeable to the second polymerizable composition.

IPC 8 full level
H01L 21/302 (2006.01); **B82Y 10/00** (2011.01); **B82Y 40/00** (2011.01); **G03F 7/00** (2006.01); **G03F 7/027** (2006.01); **H01L 21/461** (2006.01)

CPC (source: EP US)
B82Y 10/00 (2013.01 - EP US); **B82Y 40/00** (2013.01 - EP US); **G03F 7/0002** (2013.01 - EP US); **G03F 7/027** (2013.01 - EP US); **Y10T 428/24612** (2015.01 - EP US)

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MT NL NO PL PT RO SE SI SK TR

Designated extension state (EPC)
AL BA MK RS

DOCDB simple family (publication)
US 2009053535 A1 20090226; CN 101816062 A 20100825; EP 2188831 A1 20100526; EP 2188831 A4 20111123; EP 2188831 B1 20151202; JP 2010541193 A 20101224; JP 5439374 B2 20140312; KR 101538359 B1 20150722; KR 20100080897 A 20100713; SG 183079 A1 20120830; TW 200918288 A 20090501; TW I392577 B 20130411; US 2012288686 A1 20121115; WO 2009029246 A1 20090305

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US 19695908 A 20080822; CN 200880104773 A 20080825; EP 08795566 A 20080825; JP 2010522918 A 20080825; KR 20107005881 A 20080825; SG 2012055166 A 20080825; TW 97132365 A 20080825; US 2008010063 W 20080825; US 201213546622 A 20120711